

AMENDMENT TO THE CLAIMS:

1-9. (Canceled)

10. (Original) A thin film transistor comprising a semiconductor film, a first gate insulating film, a second gate insulating film and a gate electrode sequentially formed on one major surface of a substrate in that order,

whrcin said first gate insulating film covers said semiconductor film, and
said second gate insulating film is made of a material for supplying hydrogen to said
semiconductor film and has a smaller film thickness in a region not covered with said gate
electrode than that in a region covered with said gate electrode.

11. (Original) The thin film transistor according to claim 10, whrcin said first gate insulating film is a silicon oxide film and said second gate insulating film is a silicon nitride film.

12. (Original) The thin film transistor according to claim 10, wherein said semiconductor film is a poly-silicon film.